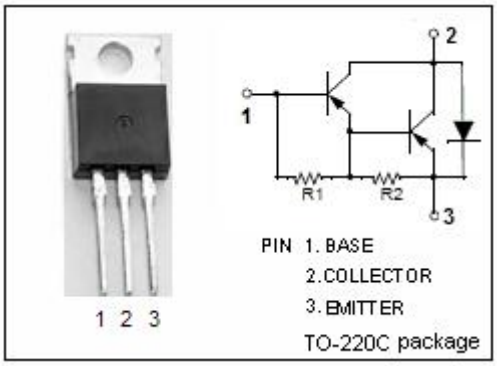
isc Silicon PNP Darlington Power Transistor 2SB669



DESCRIPTION

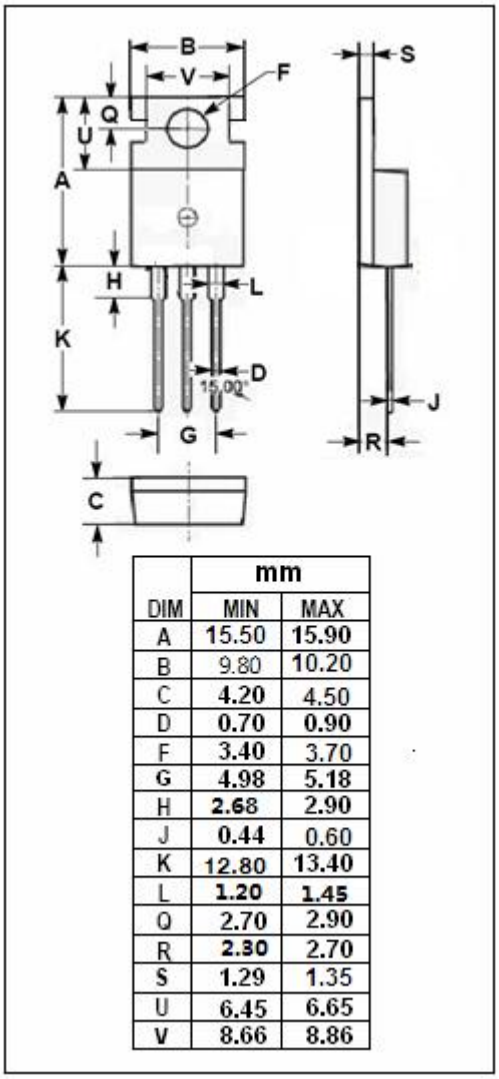
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -70V(Min)
- High DC Current Gain
  : h_{FE}= 2000(Min) @I_C= -1A
- Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-70	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
I_{CP}	Collector Current-Peak	-6	A
I_B	Base Current-Continuous	-0.3	A
P_C	Collector Power Dissipation @ T_a=25℃	2	W
	Collector Power Dissipation @ T_C=25℃	40	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; I_B= 0	-70			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -2mA; I_C= 0	-5			V
$V_{(BR)CBO}$	Collector-Base breakdown voltage	I_C=-1mA; I_E= 0	-70			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -6mA			-2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -3A; I_B= -6mA			-2.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -70V; I_E= 0			-0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= -70V; I_B= 0			-0.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-2	mA
$h_{FE\ -1}$	DC Current Gain	I_C= -1A ; V_{CE}= -3V	2000			
$h_{FE\ -2}$	DC Current Gain	I_C= -4A ; V_{CE}= -3V	750			